HIGH SPEED 36K (4K X 9) SYNCHRONOUS • DUAL-PORT RAM

Features

- High-speed clock-to-data output times
 - Military: 20/25ns (max.)
- Commercial: 12/15/20ns (max.)
- Low-power operation
 - IDT70914S Active: 850 mW (typ.) Standby: 50 mW (typ.)
- Architecture based on Dual-Port RAM cells

 Allows full simultaneous access from both ports
- Synchronous operation
 - 4ns setup to clock, 1ns hold on all control, data, and address inputs
 - Data input, address, and control registers

- Fast 12ns clock to data out
- Self-timed write allows fast cycle times
- 16ns cycle times, 60MHz operation
- TTL-compatible, single 5V (± 10%) power supply
- Clock Enable feature
- Guaranteed data output hold times
- Available in 68-pin PLCC, and 80-pin TQFP
- Military product compliant to MIL-PRF-38535 QML
- Industrial temperature range (-40°C to +85°C) is available for selected speeds.
- Recommended for replacement of IDT7099 (4K x 9) if separate 9th bit data control signals are not required.



3490 drw 01

OCTOBER 2008

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IDT70914S

High-Speed 36K (4K x 9) Synchronous Dual-Port Static RAM

Military, Industrial and Commercial Temperature Ranges

Description

The IDT70914 is a high-speed 4K x 9 bit synchronous Dual-Port RAM. The memory array is based on Dual-Port memory cells to allow simultaneous access from both ports. Registers on control, data, and address inputs provide low set-up and hold times. The timing latitude provided by this approach allow systems to be designed with very short cycle times. With an input data register, this device has been optimized for applications having unidirectional data flow or bi-directional data flow in bursts.

The IDT70914 utilizes a 9-bit wide data path to allow for parity at the user's option. This feature is especially useful in data communication applications where it is necessary to use a parity bit for transmission/

reception error checking.

Fabricated using IDT's CMOS high-performance technology, these Dual-Ports typically operate on only 850mW of power at maximum high-speed clock-to-data output times as fast as 12ns. An automatic power down feature, controlled by $\overline{\text{CE}}$, permits the on-chip circuitry of each port to enter a very low standby power mode.

The IDT70914 is packaged in a 68-pin PLCC, and an 80-pin TQFP. Military grade product is manufactured in compliance with the latest revision of MIL-PRF-38535 QML, making it ideally suited for military temperature applications demanding the highest level of performance and reliability.



Pin Configurations^(1,2,3)

- 1. All Vcc pins must be connected to power supply.
- 2. All ground pins must be connected to ground supply.
- 3. J68-1 package body is approximately .95 in x .95 in x .17 in.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

Pin Configuration^(1,2,3) (con't.)



- 1. All Vcc pins must be connected to power supply.
- 2. All ground pins must be connected to ground supply.
- 3. PN80-1 package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

IDT70914S High-Speed 36K (4K x 9) Synchronous Dual-Port Static RAM

Military, Industrial and Commercial Temperature Ranges

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Military	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
VTERM ⁽²⁾	Terminal Voltage	-0.5 to Vcc	-0.5 to Vcc	V
Tbias	Temperature Under Bias	-55 to +125	-65 to +135	۰C
Tstg	Storage Temperature	-65 to +150	-65 to +150	٥C
Іоит	DC Output Current	50	50	mA

NOTES:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq Vcc + 10%.

Capacitance

 $(TA = +25^{\circ}C, f = 1.0MHz)$ TQFP Only

	Symbol	Parameter	Conditions	Max.	Unit
	Cin	Input Capacitance	ViN = 3dV	8	pF
ſ	Соит	Output Capacitance	Vout = 3dV	9	pF
	NOTEC				

NOTES:

1. These parameters are determined by device characterization, but are not production tested.

3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.

Maximum Operating Temperature and Supply Voltage^(1,2)

Grade	Ambient Temperature	GND	Vcc
Military	-55°C to+125°C	0V	5.0V <u>+</u> 10%
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

NOTES:

3490 tbl 01

1. This is the parameter TA. This is the "instant on" casae temperature.

2. Industrial temperature: for specific speeds, packages and powers contact your

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Мах.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
V⊮	Input High Voltage	2.2		6.0 ⁽²⁾	V
VIL	Input Low Voltage	-0.5 ⁽¹⁾		0.8	۷
3490 tbl					

NOTES:

1. VIL \geq -1.5V for pulse width less than 10ns.

2. VTERM must not exceed Vcc + 10%.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (Vcc = 5.0V ± 10%)

			70914S		
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
lu	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, $VIN = 0V$ to Vcc		10	μA
ILO	Output Leakage Current	\overline{CE} = VIH, VOUT = 0V to VCC	I	10	μA
Vol	Output Low Voltage	Iol = +4mA	I	0.4	V
Vон	Output High Voltage	Ioh = -4mA	2.4		V

NOTE:

1. At Vcc < 2.0V, input leakages are undefined

3490 tb105

3490 tbl 02

Military, Industrial and Commercial Temperature Ranges

3490 tbl 06b

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(4,5) (Vcc = 5V ± 10%)

				7091	4S12 Only		4S15 Only	
Symbol	Parameter	Test Condition	Version	Typ. ⁽²⁾	Мах.	Тур. ⁽²⁾	Мах.	Unit
lcc	Dynamic Operating Current	\overline{CEL} and $\overline{CER} = VIL$,	COM'L	190	310	180	300	mA
	(Both Ports Active)	Outputs Disabled $f = f_{MAX}^{(1)}$	MIL & IND					
ISB1	Standby Current CEL and CER = VH		COM'L	95	150	90	140	mA
	(Both Ports - TTL Level Inputs)	$f = fMAX^{(1)}$	MIL & IND					
ISB2	Standby Current (One Port - TTL	$\label{eq:cells} \begin{array}{l} \overline{C}\overline{E}^{}_{A^*} = V_{IL} \text{ and } \\ \overline{C}\overline{E}^{}_{B^*} = V_{IH}^{(3)} \\ \text{Active Port Outputs } \\ \text{Disabled, } f=f_{MAx}^{(1)} \end{array}$	COM'L	170	220	160	210	mA
	Level Inputs)		MIL & IND		_	_	_	
ISB3	Full Standby	Both Ports \overline{CE}_R and	COM'L	10	15	10	15	mA
	Current (Both Ports - All CMOS Level Inputs)		MIL & IND	-				
ISB4	Full Standby Current (One Port - All CMOS	$\label{eq:constraint} \begin{array}{ c c } \overline{C}\overline{E}^*A^* &\leq 0.2V \text{ and} \\ \overline{C}\overline{E}^*B^* &\geq V \text{CC} - 0.2V^{(3)} \end{array}$	COM'L	165	210	155	200	mA
	Level Inputs)	$V_{IN} \ge \overline{V}_{CC} - 0.2V$ or $V_{IN} \le 0.2V$, Active Port Outputs Disabled $f = fmax^{(1)}$	MIL & IND			_		

3490 tbl 06a 70914S20 70914S25 Com'l & Military Military Only Parameter **Test Condition** Version Typ.⁽²⁾ Max. Typ.⁽²⁾ Symbol Мах. Unit \overline{CEL} and $\overline{CER} = VIL$, COM'L 290 Dynamic Operating 170 mΑ ICC. Current Outputs Disabled (Both Ports Active) MIL & 170 310 160 290 $f = fMAX^{(1)}$ IND Standby Current COM'L **I**SB1 \overline{CE}_{L} and $\overline{CE}_{R} = V_{H}$ 85 130 mΑ (Both Ports - TTL $f = fMAX^{(1)}$ Level Inputs) MIL & 85 140 80 130 IND **I**SB2 Standby Current COM'L mΑ CE"A" = VIL and 150 200 (One Port - TTL $\overline{C}\overline{E}^{"B"} = VIH^{(3)}$ Level Inputs) Active Port Outputs MIL & 150 210 140 200 Disabled, f=fMAX(1) IND Full Standby Both Ports \overline{CER} and COM'L mΑ ISB3 10 15 $\frac{\text{Dotter ords operations oper$ Current (Both Ports - All CMOS MIL & 10 20 10 20 Level Inputs) IND Full Standby \overline{CE} "A" $\leq 0.2V$ and COM'L 190 mΑ **I**SB4 145 \overline{CE} "B" \geq VCC - 0.2V⁽³⁾ Current (One VIN ≥ Vcc - 0.2V or Port - All CMOS Level Inputs) MIL & 145 200 135 190 $V_{IN} \leq 0.2V$, Active Port IND Outputs Disabled $f = f_{MAX}^{(1)}$

NOTES:

1. At fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcvc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

4. Vcc = 5V, $T_A = 25^{\circ}C$ for Typ, and are not production tested. Icc Dc = 150mA (Typ).

5. Industrial temperature: for specific speeds, packages and powers contact your sales office.

5

IDT70914S High-Speed 36K (4K x 9) Synchronous Dual-Port Static RAM

Military, Industrial and Commercial Temperature Ranges

AC Test Conditions

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1,2 and 3

3490 tbl 07



Figure 1. AC Output Test load.

Figure 2. Output Test Load (For tckLz, tckHz, toLz, and toHz). *Including scope and jig.



Figure 3. Typical Output Derating (Lumped Capacitive Load).

10

9

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35

15

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0

6

2

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0

5

2

12

11

45

20

ns

ns

ns

ns

ns

ns

ns 3490 tbl 08b

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing) $^{\rm (3)}$

	ercial: Vcc = 5V ± 10%, TA = 0°C to +70°C; Military: `	7091	4S12 I Only	7091	I4S15 I Only	
Symbol	Parameter	Min.	Мах.	Min.	Max.	Uni
tcyc	Clock Cycle Time	16		20		ns
tсн	Clock High Time	6		6		ns
tcL	Clock Low Time	6		6		ns
tcp	Clock High to Output Valid		12		15	ns
ts	Registered Signal Set-up Time	4		4		ns
tн	Registered Signal Hold Time	1		1		n
tDC	Data Output Hold After Clock High	3		3		n
t CKLZ	Clock High to Output Low-Z ^(1,2)	2		2		n
tскнz	Clock High to Output High-Z ^(1,2)		7		7	n
toe	Output Enable to Output Valid	_	7		8	n
tolz	Output Enable to Output Low-Z ^(1,2)	0		0		n
tонz	Output Disable to Output High-Z ^(1,2)		7		7	n
tscк	Clock Enable, Disable Set-up Time	4		4		n
tнск	Clock Enable, Disable Hold Time	2		2		n
rt-to-Port D	lelay	-				-
tcwdd	Write Port Clock High to Read Data Delay	_	25		30	n
tcss	Clock-to-Clock Setup Time		13	—	15	n
			-			3490 tb
		Cor	4S20 n'I & itary	Mili	70914S25 Military Only	
Symbol	Parameter	Min.	Мах.	Min.	Max.	Un
tcyc	Clock Cycle Time	20		25		n
tсн	Clock High Time	8		10		n
tcL	Clock Low Time	8		10		n
tcp	Clock High to Output Valid		20		25	n
ts	Registered Signal Set-up Time	5	_	6		n
tн	Registered Signal Hold Time	1	—	1		n
tрс	Data Output Hold After Clock High	3		3		n
t CKLZ	Clock High to Output Low-Z ^(1,2)	2		2		n
TONEL	5					

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1. Transition is measured 0mV from Low or High impedance voltage with the Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization, but is not production tested.

Output Enable to Output Valid

Output Enable to Output Low-Z^(1,2)

Output Disable to Output High-Z^(1,2)

Clock Enable, Disable Set-up Time

Clock Enable, Disable Hold Time

Clock-to-Clock Setup Time

Write Port Clock High to Read Data Delay

toe

tolz

tonz

tscĸ

tнск

tcss

NOTES:

Port-to-Port Delay tcwdd Wr

3. Industrial temperature: for specific speeds, packages and powers contact your sales office.

Timing Waveform of Read Cycle, Either Side



Timing Waveform of Write with Port-to-Port Read^(2,3,4)



- 1. Transition is measured ±200mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. $\overline{CE}_{L} = \overline{CE}_{R} = V_{IL}, \overline{CLKEN}_{L} = \overline{CLKEN}_{R} = V_{IL}.$
- 3. \overline{OE} = VIL for the reading port, port 'B'.
- 4. All timing is the same for left and right ports. Ports "A" may be either the left or right port. Port "B" is opposite from port "A".
- 5. If tccs < maximum specified, then data from right port READ is not valid until the maximum specified for tcwpp.
- If tccs > maximum specified, then data from right port READ is not valid until tccs + tcb. tcvbb does not apply in this case.

Timing Waveform of Read-to-Write Cycle No. $1^{(1,2)}$ (tcyc = min.)



Timing Waveform of Read-to-Write Cycle No. $2^{(4)}$ (tcyc > min.)



3490 drw 11

- For tcyc = min.; data out coincident with the rising edge of the subsequent write clock can occur. To ensure writing to the correct address location, the write must be repeated on the second write clock rising edge. If CE = VIL, invalid data will be written into array. The An+1 must be rewritten on the following cycle.
 OE LOW throughout.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. For tcyc > min.; OE may be used to avoid data out coincident with the rising edge of the subsequent write clock. Use of OE will eliminate the need for the write to be repeated.

IDT70914S

High-Speed 36K (4K x 9) Synchronous Dual-Port Static RAM

Military, Industrial and Commercial Temperature Ranges

Functional Description

The IDT70914 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide very short set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal. An asynchronous output enable is provided to ease asynchronous bus interfacing.

The internal write pulse width is dependent on the LOW to HIGH

transitions of the clock signal allowing the shortest possible realized cycle times. Clock enable inputs are provided to stall the operation of the address and data input registers without introducing clock skew for very fast interleaved memory applications.

A HIGH on the \overline{CE} input for one clock cycle will power down the internal circuitry to reduce static power consumption.

Truth Table I: Read/Write Control⁽¹⁾

	Inputs		Outputs		
Sy	nchronou	IS ⁽³⁾	Asynchronous		
CLK	ĒĒ	R/W	ŌĒ	I/O0-8	Mode
\uparrow	Н	Х	Х	High-Z	Deselected, Power-Down
\uparrow	L	L	Х	DATAIN	Selected and Write Enabled
\uparrow	L	Н	L	DATAOUT	Read Selected and Data Output Enable Read
\uparrow	Х	Х	Н	High-Z	Outputs Disabled

3490 tbl 09

Truth Table II: Clock Enable Function Table⁽¹⁾

	Inputs		Registe	r Inputs	Register Outputs ⁽⁴⁾	
Mode	CLK ⁽³⁾	CLKEN ⁽²⁾	ADDR	DATAIN	ADDR	DATAOUT
Load "1"	Ŷ	L	Н	Н	Н	Н
Load "0"	Ŷ	L	L	L	L	L
Hold (do nothing)	Ŷ	Н	Х	Х	NC	NC
Ϋ́, Ϋ́,	Х	Н	Х	Х	NC	NC
3490 tb110						

NOTES:

1. 'H' = HIGH voltage level steady state, 'h' = HIGH voltage level one set-up time prior to the LOW-to-HIGH clock transition, 'L' = LOW voltage level steady state 'l' = LOW voltage level one set-up time prior to the LOW-to-HIGH clock transition, 'X' = Don't care, 'NC' = No change

2. CLKEN = VIL must be clocked in during Power-Up.

3. Control signals are initialted and terminated on the rising edge of the CLK, depending on their input level. When R/W and CE are LOW, a write cycle is initiated on the LOW-to-HIGH transition of the CLK. Termination of a write cycle is done on the next LOW-to-HIGH transistion of the CLK.

4. The register outputs are internal signals from the register inputs being clocked in or disabled by CLKEN.

IDT70914S

Ordering Information



NOTE:

1. Industrial temperature range is available on selected TQFP packages in standard power. For specific speeds, packages and powers contact your sales office.

Datasheet Document History

3/10/99:	Initiated datasheet document history
	Converted to new format
	Cosmetic and typographical corrections
	Page 2 and 3 Added additional notes to pin configurations
6/7/99:	Changed drawing format
11/10/99:	Replaced IDT logo
5/24/00:	Page 4 Increased storage temperature parameter
	Clarified TA parameter
	Page 5 DC Electrical parameters-changed wording from "open" to "disabled"
	Changed ±200mV to 0mV in notes
1/12/01:	Removed PGA pinout (obsolete package)
	Changed cycle time of 12ns part from 17ns (58MHz) to 16ns (60MHz)
10/21/08:	Page 11 Removed "IDT" from orderable part number



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